

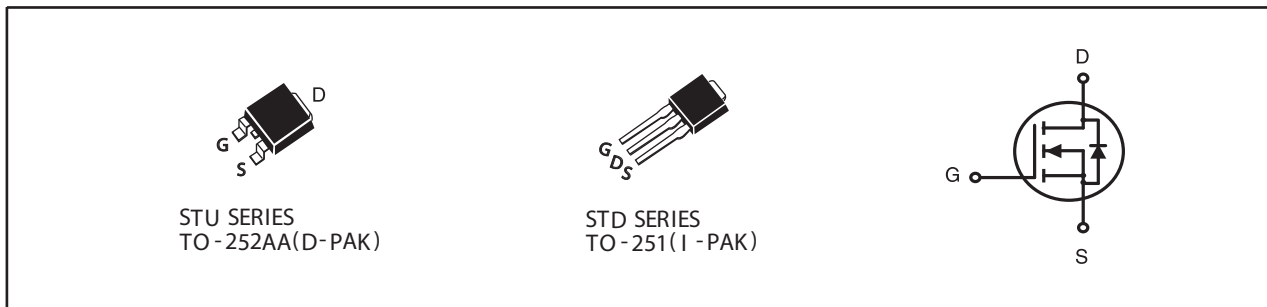


N-Channel Logic Level Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
60V	18A	55 @ V _{GS} =10V
		68 @ V _{GS} =4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Limit	Units
V _{DS}	Drain-Source Voltage	60	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous ^a	T _C =25°C	18
		T _C =70°C	14.5
I _{DM}	-Pulsed ^b	72	A
E _{AS}	Single Pulse Avalanche Energy ^d	25	mJ
P _D	Maximum Power Dissipation ^a	T _C =25°C	36
		T _C =70°C	23
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

THERMAL CHARACTERISTICS

R _{θJC}	Thermal Resistance, Junction-to-Case ^a	3.5	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient ^a	50	°C/W

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ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =48V, V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V, V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1.0	1.8	3.0	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =18A		45	55	m ohm
		V _{GS} =4.5V, I _D =16.2A		50	68	m ohm
g _{FS}	Forward Transconductance	V _{DS} =30V, I _D =18A		16		S
DYNAMIC CHARACTERISTICS ^c						
C _{ISS}	Input Capacitance	V _{DS} =30V, V _{GS} =0V f=1.0MHz		825		pF
C _{OSS}	Output Capacitance			72		pF
C _{RSS}	Reverse Transfer Capacitance			48		pF
SWITCHING CHARACTERISTICS ^c						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =30V I _D =1A V _{GS} =10V R _{GEN} =3.3 ohm		13		ns
t _r	Rise Time			12.5		ns
t _{D(OFF)}	Turn-Off Delay Time			38		ns
t _f	Fall Time			6		ns
Q _g	Total Gate Charge	V _{DS} =30V, I _D =18A, V _{GS} =10V		13.5		nC
		V _{DS} =30V, I _D =18A, V _{GS} =4.5V		6.3		nC
Q _{gs}	Gate-Source Charge	V _{DS} =30V, I _D =18A, V _{GS} =10V		1.6		nC
Q _{gd}	Gate-Drain Charge			3.4		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
I _S	Maximum Continuous Drain-Source Diode Forward Current				1.7	A
V _{SD}	Diode Forward Voltage ^b	V _{GS} =0V, I _S =1.7A		0.79	1.3	V

Notes

- Surface Mounted on FR4 Board, t ≤ 10sec.
- Pulse Test: Pulse Width ≤ 300us, Duty Cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.
- Starting T_J=25°C, L=0.5mH, V_{DD} = 30V. (See Figure 13)

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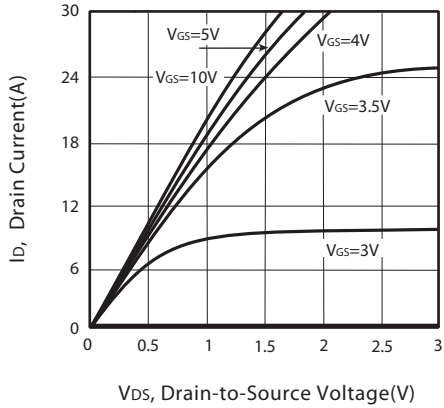


Figure 1. Output Characteristics

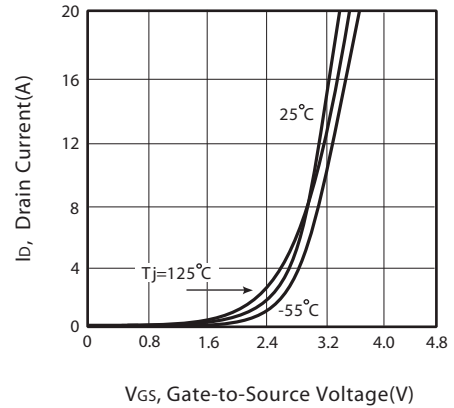


Figure 2. Transfer Characteristics

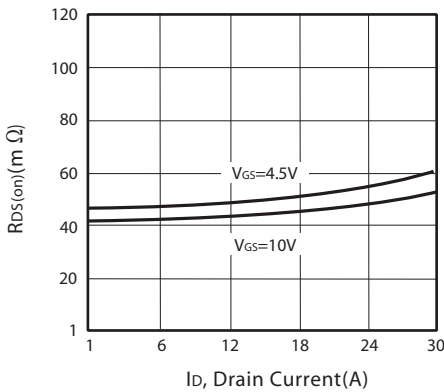


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

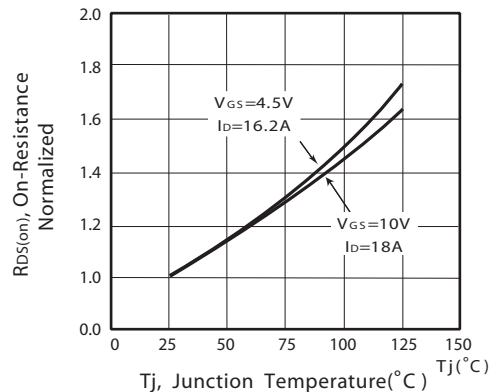


Figure 4. On-Resistance Variation with Drain Current and Temperature

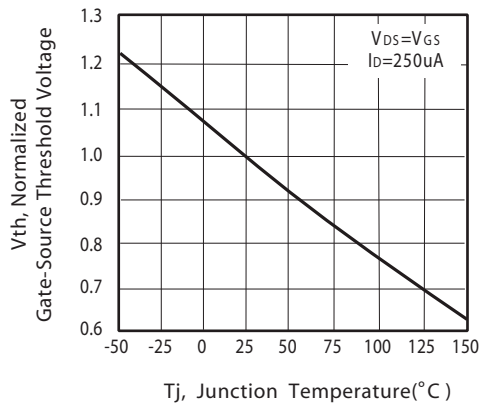


Figure 5. Gate Threshold Variation with Temperature

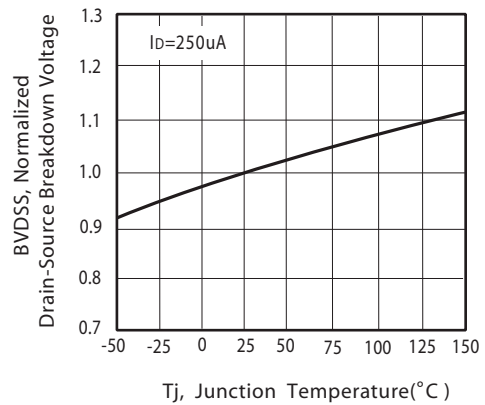


Figure 6. Breakdown Voltage Variation with Temperature

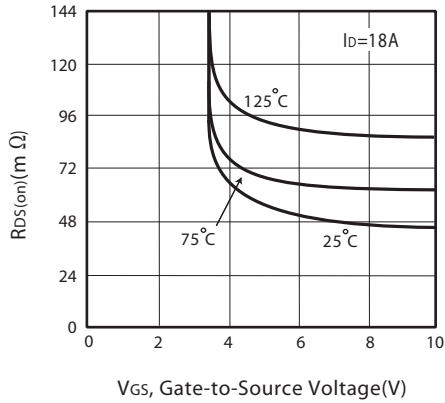


Figure 7. On-Resistance vs. Gate-Source Voltage

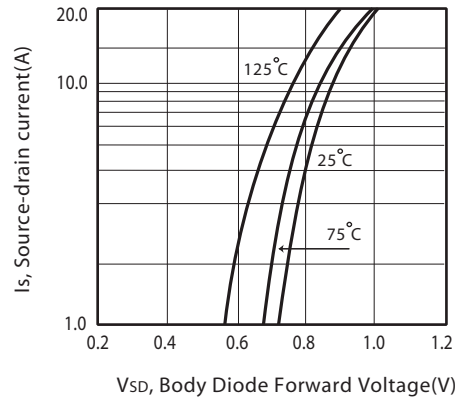


Figure 8. Body Diode Forward Voltage Variation with Source Current

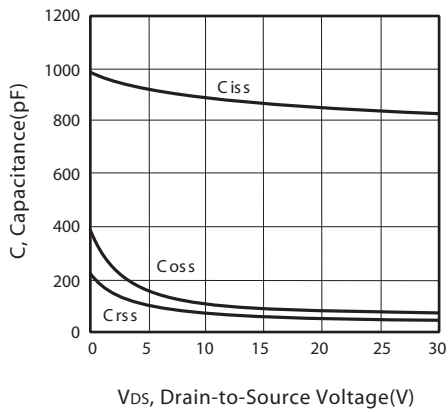


Figure 9. Capacitance

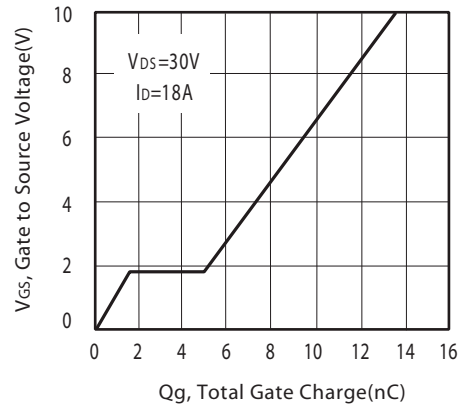


Figure 10. Gate Charge

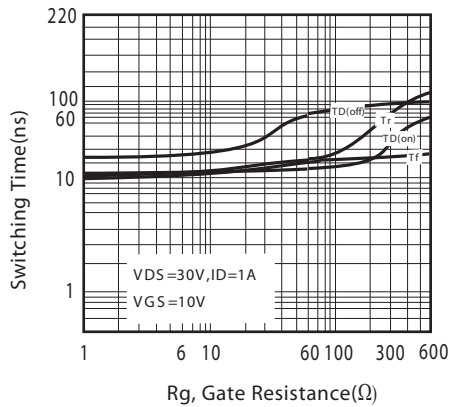


Figure 11. switching characteristics

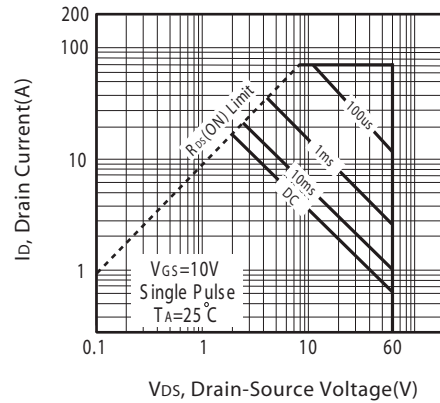
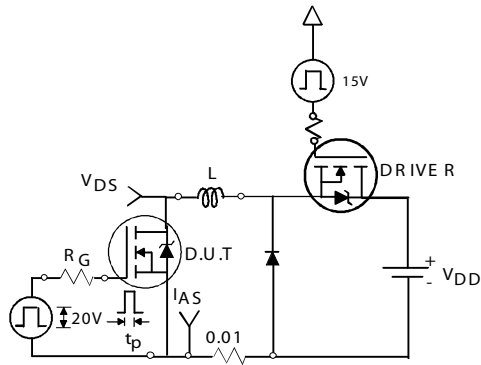
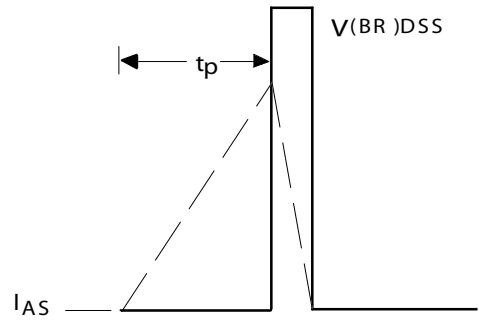


Figure 12. Maximum Safe Operating Area



Unclamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

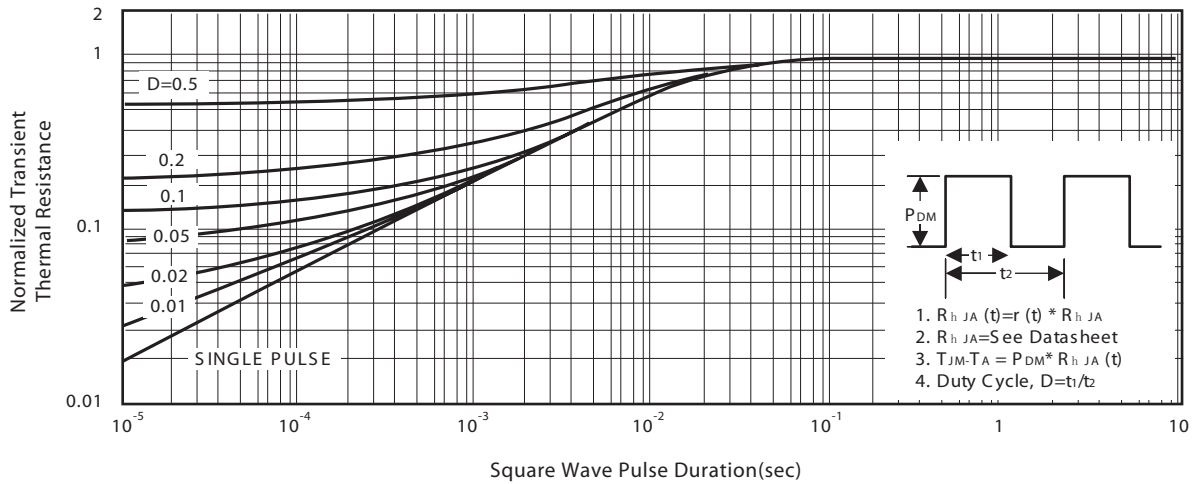
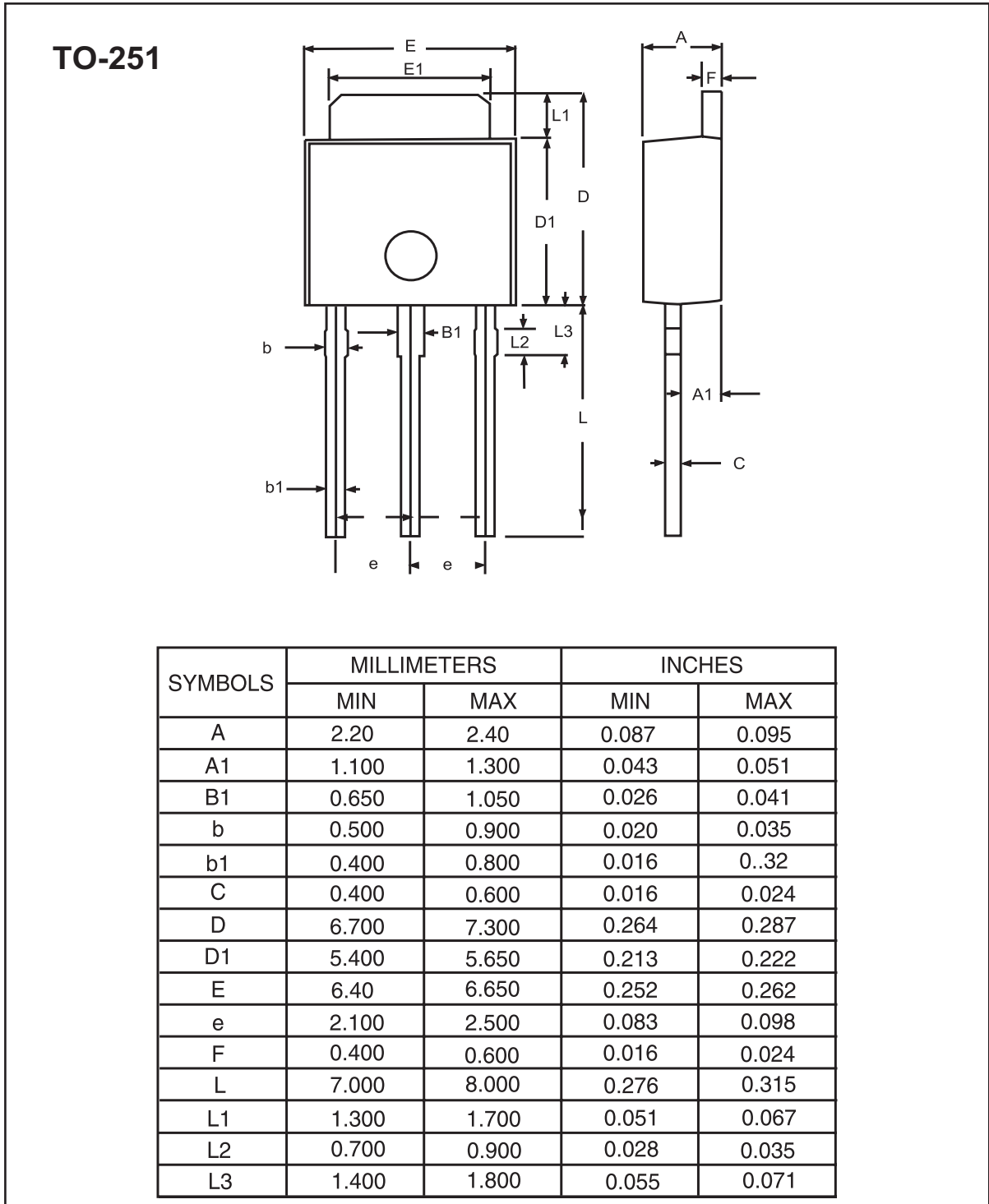


Figure 14. Normalized Thermal Transient Impedance Curve

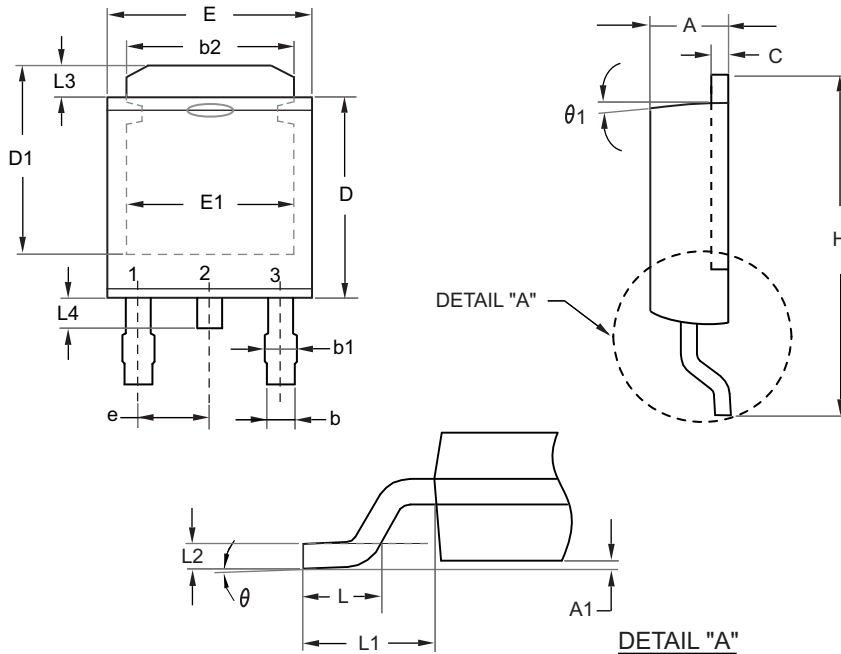
PACKAGE OUTLINE DIMENSIONS



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TO-252

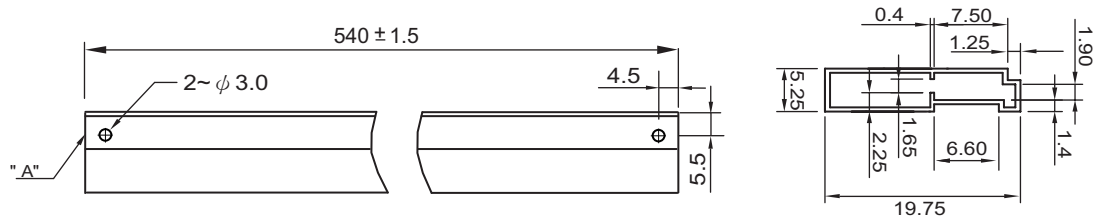


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.184	2.388	0.086	0.094
A1	0.000	0.127	0.000	0.005
b	0.633	0.889	0.025	0.035
b1	0.666	1.092	0.026	0.043
b2	5.207	5.461	0.205	0.215
C	0.460	0.584	0.018	0.023
D	5.969	6.223	0.235	0.245
D1	5.415	5.515	0.213	0.217
E	6.400	6.731	0.252	0.265
E1	4.902	5.004	0.193	0.197
e	2.286	BSC	0.090	BSC
H	9.601	10.286	0.378	0.405
L	1.313	1.651	0.052	0.065
L1	2.666	3.174	0.105	0.125
L2	0.460	0.560	0.018	0.022
L3	0.889	1.143	0.035	0.045
L4	0.508	1.016	0.020	0.040
θ	0°	8°	0°	8°
θ_1	7°	REF.	7°	REF.

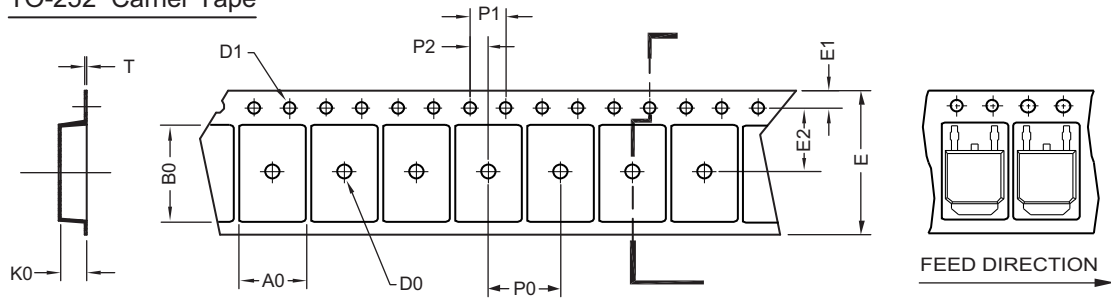
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TO-251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



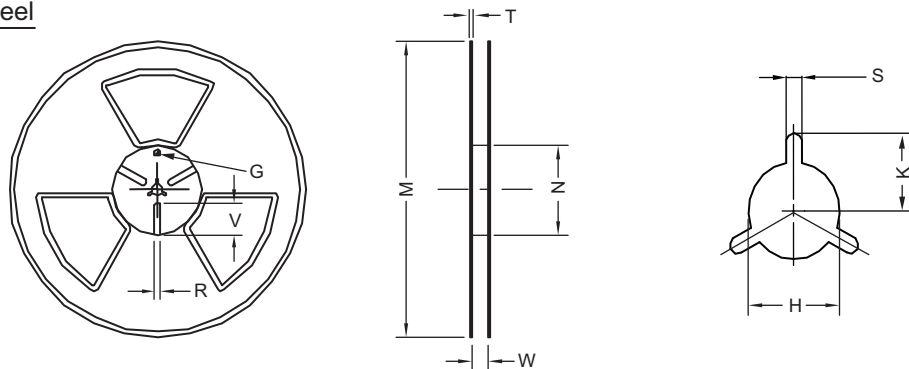
TO-252 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 mm)	6.96 ±0.1	10.49 ±0.1	2.79 ±0.1	φ 2	φ 1.5 +0.1 - 0	16.0 ±0.3	1.75 ±0.1	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

TO-252 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	φ 330	φ 330 ± 0.5	φ 97 ± 1.0	17.0 + 1.5 - 0	2.2	φ 13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---